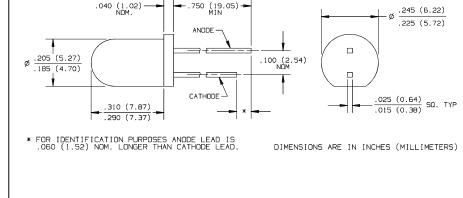


PIN Silicon Photodiode Type OP999





Features

- Narrow receiving angle
- Linear response vs. irradiance
- Fast switching time
- T-1 3/4 package style

Description

The OP999 photodiode consists of a PIN silicon photodiode mounted in a dark blue plastic injection molded shell package. The narrow receiving angle provides excellent on-axis coupling. The sensors are 100% production tested for close correlation with Optek GaAlAs emitters.

Optek's packaging process provides excellent optical and mechanical axis alignment. The shell also provides excellent optical lens surface, control of chip placement, and consistency of the outside package dimensions.

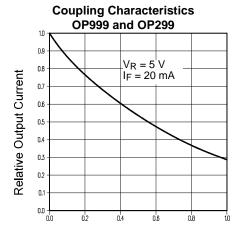
Absolute Maximum Ratings (T_A = 25^o C unless otherwise noted)

Reverse Breakdown Voltage	60 V
Storage and Operating Temperature Range40° C to	+100° C
Lead Soldering Temperature (1/16 inch [1.6 mm] from case for 5 sec. with	
soldering iron)	260° C ⁽¹⁾
Power Dissipation	00 mW ⁽²⁾
Natao	

- (1) RMA flux is recommended. Duration can be extended to 10 sec. max. when flow soldering. Max. 20 grams force may be applied to leads when soldering. Derate linearly 1.67 mW/ $^{\circ}$ C above 25 $^{\circ}$ C.
- (3) Light source is an unfiltered GaAlAs emitting diode operating at peak emission wavelength of 890 nm and $E_{e(APT)}$ of 0.25 mW/cm²
- (4) This dimension is held to within ± 0.005 " on the flange edge and may vary up to ± 0.020 " in the area of the leads.

Typical Performance Curves

Relative Response vs. Wavelength Relative Response -0.0 -600 λ - Wavelength - nm



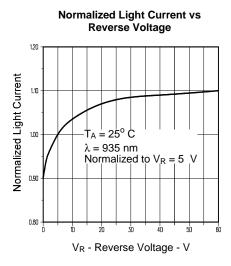
Distance Between Lens Tips - inches

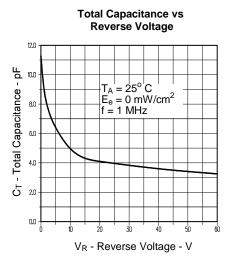
Type OP999

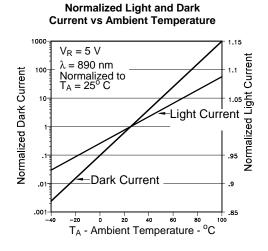
Electrical Characteristics (T_A = 25^o C unless otherwise noted)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
IL	Reverse Light Current	6.5		15	μΑ	$V_R = 5 \text{ V}, E_e = 0.25 \text{ mW/cm}^{2(3)}$
ID	Reverse Dark Current		1	60	nA	$V_R = 30 \text{ V}, E_e = 0$
V _(BR)	Reverse Breakdown Voltage	60			V	$I_R = 100 \mu A$
V _F	Forward Voltage			1.2	V	$I_F = 1 \text{ mA}$
CT	Total Capacitance		4		pF	$V_R = 20 \text{ V}, E_e = 0, f = 1.0 \text{ MHz}$
t _r , t _f	Rise Time, Fall Time		5		ns	V_R = 20 V, λ = 850 nm, R_L = 50 Ω

Typical Performance Curves



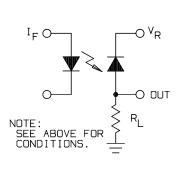




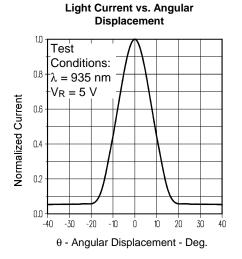
1000 $V_R = 5^{\circ} V$ $T_A = 25^{\circ} C$ I_L - Light Current - μA $\lambda = 890 \text{ nm}$

E_e - Irradiance - mW/cm²

Light Current vs. Irradiance



Switching Time Test Circuit



Optek reserves the right to make changes at any time in order to improve design and to supply the best product possible.

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Datasheets for electronic components.